

AMENDMENTS TO THE CLAIMS

Claim 1 (Currently Amended): A capacitor comprising:

a substrate;

an interlayer insulating layer formed on the substrate;

a contact plug connected to the substrate by passing through the interlayer insulating layer;

an a bottom electrode formed on the interlayer insulating layer and the contact plug;

an oxygen diffusing layer containing nitrogen on the bottom electrode;

an oxygen diffusion barrier layer containing aluminum on the electrode oxygen diffusing layer;

a dielectric layer on the oxygen diffusion barrier layer; and

a top electrode on the dielectric layer.

Claim 2 (Canceled)

Claim 3 (Original): The capacitor as recited in claim 1, wherein the bottom electrode includes hemi-spherical grains on a surface thereof.

Claim 4 (Original) the capacitor as recited in claim 1, wherein the oxygen diffusion barrier layer is an alumina layer.

Claim 5 (Currently Amended) A method for fabricating a capacitor, comprising the steps of:

a) forming an interlayer insulating layer on a substrate;

b) forming a contact plug connected to the substrate by passing through the interlayer insulating layer;

ac) forming an a bottom electrode formed on the interlayer insulating layer and the contact plug

d) forming an oxygen diffusion layer containing nitrogen on the bottom electrode;

~~b~~e) forming an oxygen diffusion barrier layer containing aluminum on the ~~bottom electrode~~oxygen diffusion layer;

[e]f) forming a dielectric layer on the oxygen diffusion barrier layer; and

~~d~~g) forming a top electrode on the dielectric layer.

Claim 6 (Currently Amended) The method as recited in claim 5, wherein the step a) includes the steps of:

a1) forming a hemi-spherical grains on a surface of the bottom electrode;~~and~~

~~a2) forming an oxygen diffusion layer containing nitrogen on the bottom electrode.~~

Claim 7 (Original) The method as recited in claim 6, wherein the oxygen diffusion barrier layer containing nitrogen is formed by using a rapid thermal process or a plasma nitride process.

Claim 8 (Original) The method as recited in claim 5, wherein the oxygen diffusion barrier is an alumina layer.

Claim 9 (Original) The method as recited in claim 8, wherein the alumina layer is formed by using a low pressure chemical vapor deposition technique or an atomic layer deposition technique.

Claim 10 (Original) The method as recited in claim 8, wherein the alumina layer is formed at a temperature of about 350 °C to 500 °C.